



First Named Inventor	Michael Smith	INFORMATION DISCLOSURE STATEMENT FORM PTO-1449
Serial No.	10/656,636	
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Group Art Unit	2811	
Examiner Name	Unknown	
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Attorney Docket No.	400.245US01	
Title: TRENCH CORNER EFFECT BIDIRECTIONAL FLASH MEMORY CELL		Sheet 1 of 7

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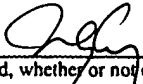
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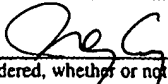
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